Power Amplifier, 4 W
27.5 - 30 GHz

Features
- High Gain: 24 dB
- P1dB: 34.8 dBm
- P3dB: 36 dBm
- IM3 Level: -23 dBc @ P_{out} = 30 dBm/tone
- Power Added Efficiency: 20% @ P3dB
- Temperature Compensated Output Power Detector
- Lead-Free 5 mm AQFN 32-lead Package
- RoHS* Compliant

Description
The MAAP-011250 is a balanced 4 W, 4-stage power amplifier assembled in a lead-free 5 mm 32-lead AQFN plastic package. This power amplifier operates from 27.5 to 30 GHz and provides 24 dB of linear gain, 4 W saturated output power and 20% efficiency while biased at 6 V.

The MAAP-011250 can be used as a power amplifier stage or as a driver stage in higher power applications. This device is ideally suited for VSAT and 28 GHz PTP applications.

This product is fabricated using a GaAs pHEMT process which features full passivation for enhanced reliability.

Ordering Information

<table>
<thead>
<tr>
<th>Part Number</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>MAAP-011250-TR0500</td>
<td>500 Piece Reel</td>
</tr>
<tr>
<td>MAAP-011250-SMB</td>
<td>Sample Board</td>
</tr>
</tbody>
</table>

1. Reference Application Note M513 for reel size information.
2. All sample boards include 3 loose parts.

* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.
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Electrical Specifications:  Freq. = 27.5 & 30 GHz, \( T_A = +25^\circ C, \ V_D = 6 \, \text{V}, \ Z_0 = 50 \, \Omega \)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Test Conditions</th>
<th>Units</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Gain</td>
<td>( P_{IN} = 0 , \text{dBm}, 27.5 , \text{GHz} )</td>
<td>dB</td>
<td>21.0</td>
<td>26.0</td>
<td>—</td>
</tr>
<tr>
<td></td>
<td>( P_{IN} = 0 , \text{dBm}, 30.0 , \text{GHz} )</td>
<td></td>
<td>21.0</td>
<td>24.5</td>
<td>—</td>
</tr>
<tr>
<td>( P_{OUT} )</td>
<td>( P_{IN} = 14.5 , \text{dBm}, 27.5 , \text{GHz} )</td>
<td>dBm</td>
<td>34.5</td>
<td>37.0</td>
<td>36.0</td>
</tr>
<tr>
<td></td>
<td>( P_{IN} = 15.0 , \text{dBm}, 30.0 , \text{GHz} )</td>
<td></td>
<td>34.5</td>
<td>36.0</td>
<td>—</td>
</tr>
<tr>
<td>IM3</td>
<td>( P_{OUT} = 30 , \text{dBm} , / , \text{tone} )</td>
<td>dBc</td>
<td>—</td>
<td>-23</td>
<td>—</td>
</tr>
<tr>
<td></td>
<td>( \text{Freq.} = 27.5 - 30 , \text{GHz} )</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Power Added Efficiency</td>
<td>( P_{IN} = 14.5 , \text{dBm} )  ( \text{Freq.} = 27.5 - 30 , \text{GHz} )</td>
<td>%</td>
<td>—</td>
<td>20</td>
<td>—</td>
</tr>
<tr>
<td>Input Return Loss</td>
<td>( P_{IN} = -20 , \text{dBm} )  ( \text{Freq.} = 27.5 - 30 , \text{GHz} )</td>
<td>dB</td>
<td>—</td>
<td>15</td>
<td>—</td>
</tr>
<tr>
<td>Output Return Loss</td>
<td>( P_{IN} = -20 , \text{dBm} )  ( \text{Freq.} = 27.5 - 30 , \text{GHz} )</td>
<td>dB</td>
<td>—</td>
<td>15</td>
<td>—</td>
</tr>
<tr>
<td>Quiescent Current</td>
<td>( I_{DSQ} ) (see bias conditions, page 4 )</td>
<td>mA</td>
<td>—</td>
<td>2300</td>
<td>—</td>
</tr>
<tr>
<td>Drain Current ( (V_{D1} + V_{D2} + V_{D3}) )</td>
<td>( P_{IN} = 14.5 , \text{dBm} )</td>
<td>mA</td>
<td>—</td>
<td>3600</td>
<td>4300</td>
</tr>
</tbody>
</table>

5. MACOM does not recommend sustained operation at power levels above 3 dB gain compression.

Maximum Operating Ratings

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Rating</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input Power (^5)</td>
<td>15 dBm</td>
</tr>
<tr>
<td>Junction Temperature ( ^6,7)</td>
<td>+160(^\circ) C</td>
</tr>
<tr>
<td>Operating Temperature</td>
<td>-40(^\circ) C to +85(^\circ) C</td>
</tr>
</tbody>
</table>

6. Operating at nominal conditions with junction temperature \( +160^\circ C \) will ensure MTTF > 1 \times 10^6 \) hours.
7. Junction Temperature \( (T_J) = T_C + \theta_{JC} * ((V * I) - (P_{OUT} - P_{IN})) \)
   Typical thermal resistance \( (\theta_{JC}) = 4^\circ \text{CW} \)
   a) For \( T_C = +25^\circ C \)
      \( T_J = +88^\circ C \) @ 6 \, \text{V}, 3.3 \, \text{A}, \, P_{OUT} = 36 \, \text{dBm}, \, P_{IN} = 14.5 \, \text{dBm} \)
   b) For \( T_C = +85^\circ C \)
      \( T_J = 146^\circ C \) @ 6 \, \text{V}, 3.0 \, \text{A}, \, P_{OUT} = 34.5 \, \text{dBm}, \, P_{IN} = 14.5 \, \text{dBm} \)

Absolute Maximum Ratings \(^8,9\)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Absolute Maximum</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input Power</td>
<td>17.5 dBm</td>
</tr>
<tr>
<td>Drain Voltage</td>
<td>+6.5 V</td>
</tr>
<tr>
<td>Gate Voltage</td>
<td>-3 to 0 V</td>
</tr>
<tr>
<td>Junction Temperature</td>
<td>+175^\circ C</td>
</tr>
<tr>
<td>Storage Temperature</td>
<td>-65^\circ C to +125^\circ C</td>
</tr>
</tbody>
</table>

8. Exceeding any one or combination of these limits may cause permanent damage to this device.
9. MACOM does not recommend sustained operation near these survivability limits.
10. Junction temperature directly effects device MTTF. Junction temperature should be kept as low as possible to maximize lifetime.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1A devices.
Sample Board Layout

Application Schematic

Parts List

<table>
<thead>
<tr>
<th>Part</th>
<th>Value</th>
<th>Case Style</th>
</tr>
</thead>
<tbody>
<tr>
<td>C1 - C8</td>
<td>0.01 µF</td>
<td>0402</td>
</tr>
<tr>
<td>C9 - C12</td>
<td>22 µF</td>
<td>0603</td>
</tr>
<tr>
<td>R1 - R8</td>
<td>10 Ω</td>
<td>0402</td>
</tr>
<tr>
<td>J1</td>
<td>jumper</td>
<td>0603</td>
</tr>
</tbody>
</table>

Sample Board Material Specifications

Top Layer: 1/2 oz Copper Cladding, 0.017 mm thickness
Dielectric Layer: Rogers RO4003C 0.203 mm thickness
Bottom Layer: 1/2 oz Copper Cladding, 0.017 mm thickness
Finished overall thickness: 0.238 mm
**Recommended PCB Layout Detail:**
RF input and output pre-matching circuit patterns are identical and are designed to compensate packaging effects. Transmission line dimensions apply to a PCB with 0.203 mm thick Rogers RO4003C laminate dielectric. Performance curves shown in this data sheet were measured with these circuit patterns.

![PCB Layout Diagram]

**Biasing Conditions**
Recommended biasing conditions are $V_D = 6$ V, $I_{DSQ} = 2.3$ A (controlled with $V_G$). The drain bias voltage range is 3 to 6 V, and the quiescent drain current biasing range is 2 to 2.5 A.

$V_G$ pins 10 and 11 are connected internally but are not connected to pin 31; $V_G$ bias must be applied to pins 31 and 10 or 11. Muting can be accomplished by setting the $V_G$ to the pinched off voltage ($V_G = -2$ V).

$V_D$ bias must be applied to all $V_{DX}$ pins ($V_{D1}$, $V_{D2}$, and $V_{D3}$) on both sides of device as these pins are not internally connected.

**Operating the MAAP-011250**

**Turn-on**
1. Apply $V_G$ (-1.5 V).
2. Apply $V_D$ (6.0 V typical).
3. Set $I_{DO}$ by adjusting $V_G$ more positive (typically -0.9 to -1.0 V for $I_{DSQ} = 2.3$ A).
4. Apply $RF_{IN}$ signal.

**Turn-off**
1. Remove $RF_{IN}$ signal.
2. Decrease $V_D$ to -1.5 V.
3. Decrease $V_D$ to 0 V.
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Typical Performance Curves: $V_D = 6\, \text{V}, \, I_{DSQ} = 2300\, \text{mA}$

**Small Signal Gain vs. Frequency over Temperature**

![Small Signal Gain vs. Frequency over Temperature graph]

**Small Signal Gain vs. Frequency over Bias Voltage**

![Small Signal Gain vs. Frequency over Bias Voltage graph]

**Input Return Loss vs. Frequency over Temperature**

![Input Return Loss vs. Frequency over Temperature graph]

**Input Return Loss vs. Frequency over Bias Voltage**

![Input Return Loss vs. Frequency over Bias Voltage graph]

**Output Return Loss vs. Frequency over Temperature**

![Output Return Loss vs. Frequency over Temperature graph]

**Output Return Loss vs. Frequency over Bias Voltage**

![Output Return Loss vs. Frequency over Bias Voltage graph]
Typical Performance Curves: $V_D = 6\,V$, $I_{DSQ} = 2300\,\text{mA}$

**P3dB vs. Frequency over Temperature**

![Graph of P3dB vs. Frequency over Temperature]

**P3dB vs. Frequency over Bias Voltage**

![Graph of P3dB vs. Frequency over Bias Voltage]

**P1dB vs. Frequency over Temperature**

![Graph of P1dB vs. Frequency over Temperature]

**P1dB vs. Frequency over Bias Voltage**

![Graph of P1dB vs. Frequency over Bias Voltage]
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Typical Performance Curves: \( V_D = 6 \) V, \( I_{DSQ} = 2300 \) mA

**Output IP3 over Temperature \( (P_{OUT} = 30 \) dBm / Tone)**

**Output IP3 over Bias Voltage \( (P_{OUT} = 30 \) dBm / Tone)**

**IM3 over Temperature \( (P_{OUT} = 30 \) dBm / Tone)**

**IM3 over Bias Voltage \( (P_{OUT} = 30 \) dBm / Tone)**
Power Amplifier, 4 W
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Typical Performance Curves: \( V_D = 6 \, \text{V}, I_{\text{DSQ}} = 2300 \, \text{mA} \)

- **P1dB, P3dB vs. Frequency**
- **Gain and PAE @ P3dB vs. Frequency**
- **IM3 vs. Output Power**
- **Output IP3 vs. Output Power**

For further information and support please visit: [https://www.macom.com/support](https://www.macom.com/support)
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Typical Performance Curves: $V_D = 6 \text{ V}$, $I_{DSQ} = 2300 \text{ mA}$

**Output Power vs. Input Power**

![Output Power vs. Input Power Graph](image)

**PAE vs. Input Power**

![PAE vs. Input Power Graph](image)

**Bias Current vs. Input Power**

![Bias Current vs. Input Power Graph](image)

**Quiescent Drain Current vs. Temperature**

![Quiescent Drain Current vs. Temperature Graph](image)

**Detector Voltage vs. Output Power @ 29 GHz**

![Detector Voltage vs. Output Power Graph](image)
Lead-Free 5 mm 32-Lead AQFN Package†

† Reference Application Note S2083 for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 3 requirements.
Plating is NiPdAu.